



YJGD085P10A

P-Channel and P-Channel Complementary MOSFET

Product Summary

V_{DS}	-100V
I_D	-17A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	85m
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	105m
100% EAS Tested	
100% V_{DS} Tested	

General Description

Trench Power MOSFET technology
 Excellent package for heat dissipation
 High density cell design for low $R_{DS(ON)}$
 Moisture Sensitivity Level 1
 Epoxy Meets UL 94 V-0 Flammability Rating
 Halogen Free

Applications

Power switching application
 Uninterruptible power supply
 DC-DC convertor

Absolute Maximum Ratings ($T_J=25$ unless otherwise noted)

Parameter			Symbol	Limit	Unit
Drain-source Voltage			V_{DS}	-100	V
Gate-source Voltage			V_{GS}	± 20	V
Continuous Drain Current (Note 1,2)	Steady-State	$T_A=25$, $V_{GS}=-10V$	I_D	-3.4	A
		$T_A=100$, $V_{GS}=-10V$		-2.1	
Continuous Drain Current (Note 1,3)	Steady-State	$T_C=25$, $V_{GS}=-10V$		-17	
		$T_C=100$, $V_{GS}=-10V$		-10.7	
Pulsed Drain Current	$T_C=25$, $t_p=100\mu s$		I_{DM}	-60	A
Avalanche energy	$V_G=-10V$, R_G , $L=0.5mH$, $I_{AS}=-16A$		EAS	64	mJ
Total Power Dissipation (Note 1,2)	Steady-State	$T_A=25$	P_D	2	W
		$T_A=100$		0.8	
Total Power Dissipation (Note 1,3)	Steady-State	$T_C=25$		59	
		$T_C=100$		23	
Junction and Storage Temperature Range			T_J, T_{STG}	-55 +150	

Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	R	50	60	/W
Thermal Resistance Junction-to-Case	Steady-State	R	1.7	2.1	

Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)
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YJGD085P10A

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-$	-100	-	-	V



YJGD085P10A

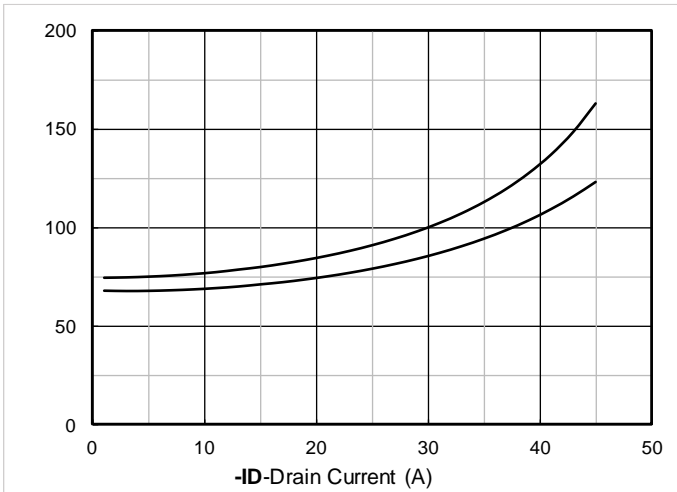


Figure 7. $R_{DS(on)}$ VS Drain Current

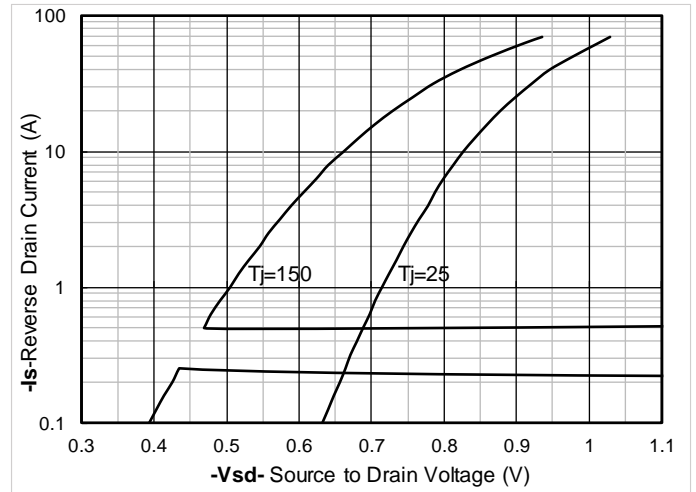


Figure 8. Forward characteristics of reverse diode

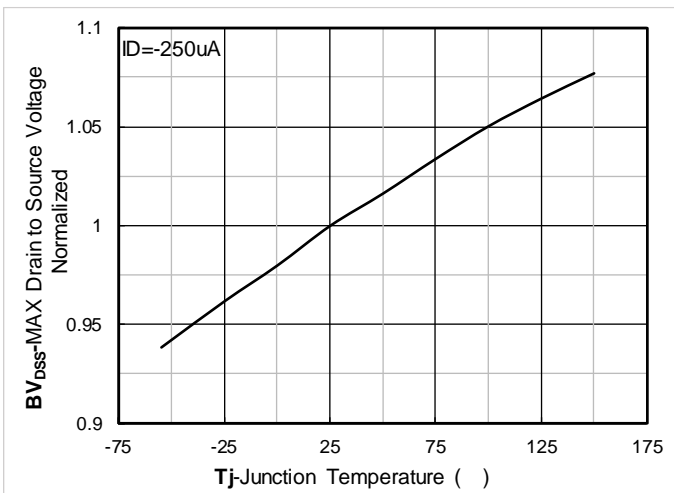


Figure 9. Normalized breakdown voltage

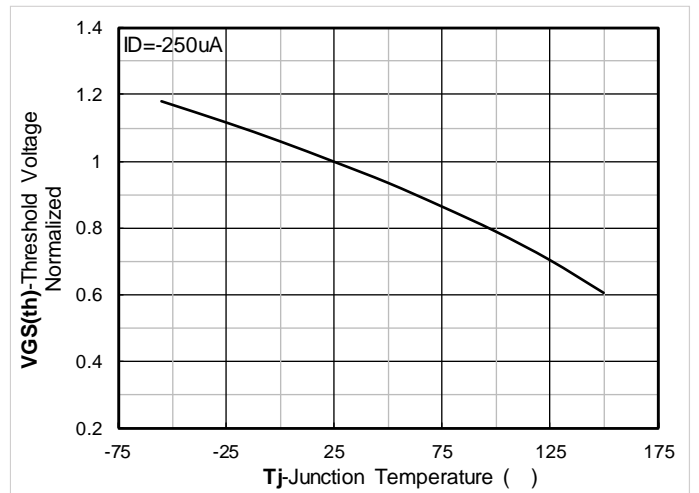


Figure 10. Normalized Threshold voltage

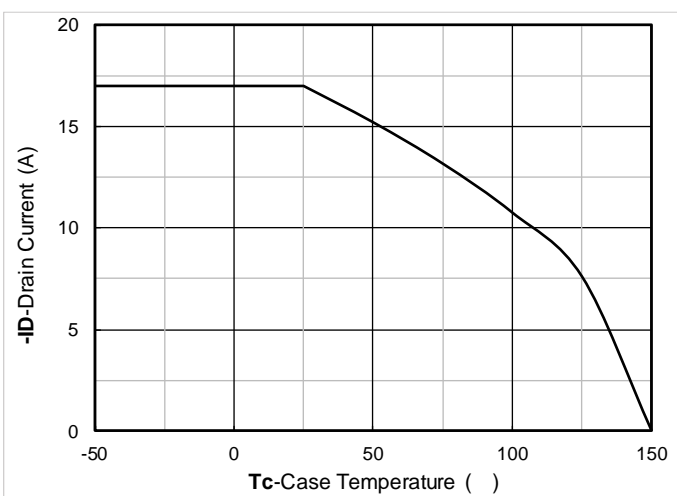


Figure 11. Current dissipation

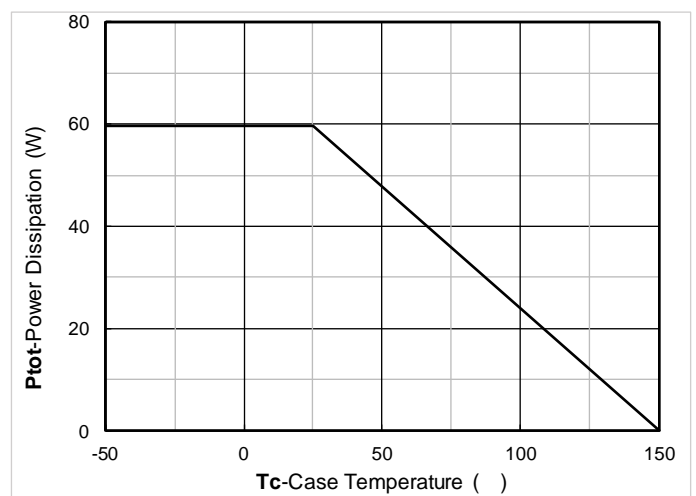


Figure 12. Power dissipation

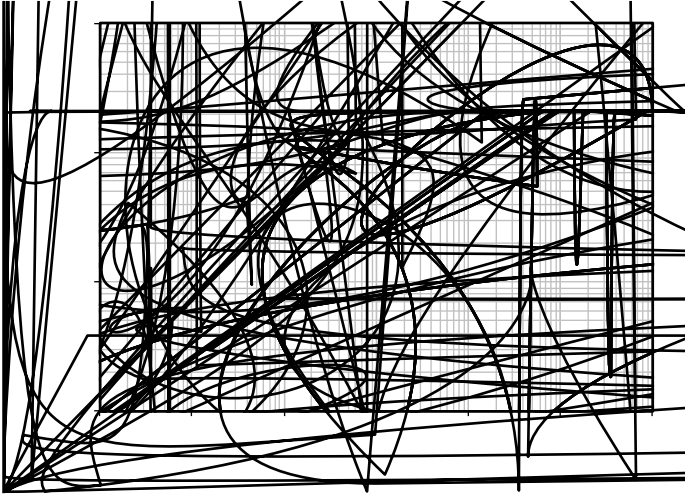
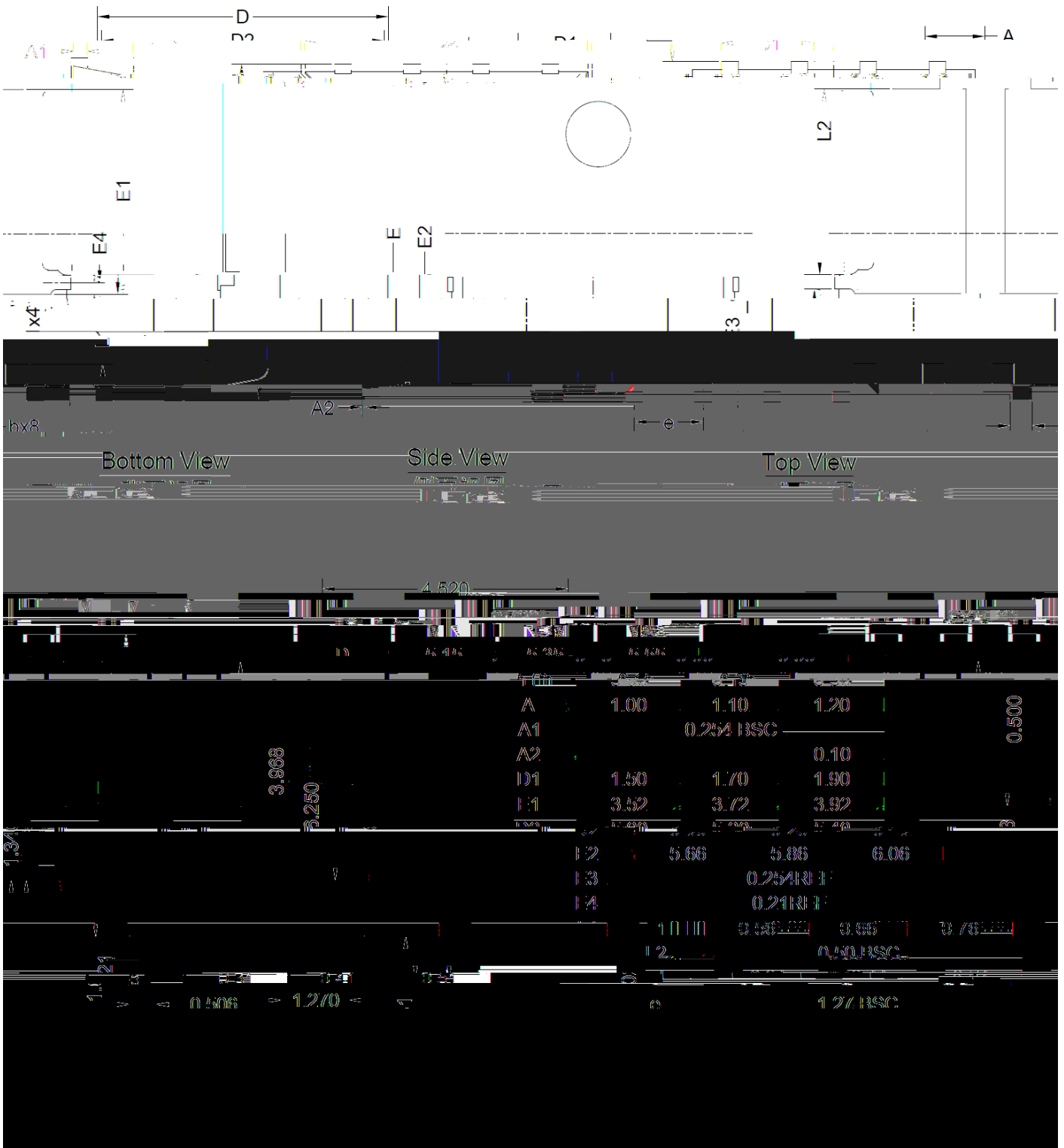


Figure 13.



YJGD085P10A

PDFN5060-8L-E-1.1mm Package information





YJGD085P10A

Disclaimer

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